



INDUSTRIAL

DDR4 WT DIMM



United States Patent / US11051392B2
Taiwan Invention Patent / I703921
China Utility Patent / CN 211019739 U

工業級Rugged series DDR4 WT DIMM採用高品質原廠工規等級IC，在系統效能與產品耐用度上有絕佳表現。且產品具有耐用型專利及專利石墨烯散熱技術，可應用於大多數嚴苛工業環境。



Main Feature

- 專利石墨烯散熱模組
美國發明專利 (證書號: US11051392B2)
台灣發明專利 (證書號: I703921)
中國新型專利 (證書號: CN 211019739 U)
- 原廠工規等級顆粒IC
- 耐用型儲存產品專利技術 (台灣新型專利: M611951)
- 專利IC分級測試驗證技術 (台灣發明專利: I751093)
- 軍規等級耐衝擊及抗震

Specification

Frequency	2133 / 2400 / 2666 / 3200
Capacity	4GB / 8GB / 16GB / 32GB
Pin Count	288pin (U-DIMM) / 260pin (SO-DIMM)
Width	64Bits
Voltage	1.2V
PCB Height	1.23 Inches (U-DIMM) / 1.18 Inches (SO-DIMM)
Standard Operating Temperature (°C)	-40~85°C
Extended Operating Temperature (°C)	-40~95°C
Shock	<ul style="list-style-type: none"> • Operation: 50G / 11ms (compliant with MIL-STD-202G Test condition A) • Non-operation: 1,500G / 0.5ms (compliant with MIL-STD-883K Test condition B)
Vibration	<ul style="list-style-type: none"> • Operation: 7.69 Grms, 20~2,000 Hz / random (compliant with MIL-STD-810G General) • Non-operation: 4.02 Grms, 15 ~ 2,000 Hz / sine (compliant with MIL-STD-810G General)
Anti-Sulfuration	✓ 台灣新型專利 (證書號: M611951)
Value-Added Service	Conformal Coating
Warranty	Limited Lifetime

Ordering Information

Frequency	Capacity	Team P/N
U-DIMM 2400	4GB	TE4GHLXV4HH-VP0G
	8GB	TE8GHLXV4BH-VP0G
	16GB	TE16GHLXV4BH-VP0G
U-DIMM 2666	8GB	TE8GHLXV6BH-VP0G
	16GB	TE16GHLXV6BH-VP0G
	32GB	TE32GHLXV6MH-VP0G
U-DIMM 3200	8GB	TE8GHLXV3BH-VP0G
	16GB	TE16GHLXV3BH-VP0G
	32GB	TE32GHLXV3MH-VP0G
SO-DIMM 2400	4GB	TE4GHSXV4HH-VP0G
	8GB	TE8GHSXV4BH-VP0G
	16GB	TE16GHSXV4BH-VP0G
SO-DIMM 2666	8GB	TE8GHSXV6BH-VP0G
	16GB	TE16GHSXV6BH-VP0G
	32GB	TE32GHSXV6MH-VP0G
SO-DIMM 3200	8GB	TE8GHSXV3BH-VP0G
	16GB	TE16GHSXV3BH-VP0G
	32GB	TE32GHSXV3MH-VP0G

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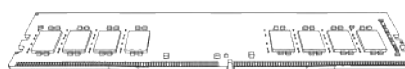
▲In a high temperature environment (95 °C)



TEAM Industrial Rugged DDR4 WT DIMM

有使用專利石墨烯散熱片

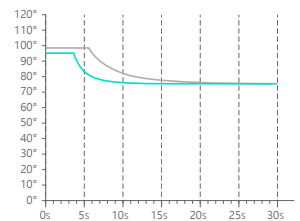
95°
Actual product surface temp



Other industrial DDR4 DIMM

無使用散熱片

99°
Actual product surface temp



※實驗數據為根據TEAMGROUP內部實驗室測試結果，利用無散熱片DDR4 DIMM與貼附石墨烯散熱片的DDR4 WT DIMM測試溫度數據而來。相關測試環境採用寬溫環境(95°C)方式，實際溫度可能依不同環境條件而有所差異。

